



GEMaC

Groupe d'Étude
de la Matière Condensée

MOCVD OF II-VI SEMICONDUCTORS

GEMaC has two MOCVD (Metal Organic Chemical Vapor Deposition) growth systems devoted to the growth of structures based II/VI semiconductors.

Horizontal reactor (SAT)

Main characteristics of the system:

Sources :

- Elements II: Zn, Mg, Cd
- Eléments VI: N₂O, O₂, t-butanol
- Doping: Al, Ga, Sb, NH₃

Carrier gas: He, H₂, Ar, N₂

Pression : 30 torr atmospheric pressure

Temperature : induction heating 1000°C

Substrate size: up to 2x2"



Vertical reactor

Main characteristics of the system:

Sources:

- Elements II: Zn, Mg
- Elements VI: N₂O, t-butanol, Se, Te, S
- Doping: Al, Ga

Carrier gas: He, H₂, Ar, N₂

Pressure: atmospheric

Temperature : heatinge RF 1000°C

Substrate size 1 to 2 cm²

